AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application. Please cancel claims 5-10 without prejudice amend claims 1 and 4 and add new claims 11-14 as follows:

LISTING OF CLAIMS:

1. (Currently Amended) A semiconductor device comprising:

an electrode formed of a flat plate portion at a bottom thereof and a cylindrical portion which extends up continuously from the flat plate portion and whose one side is open, wherein a ~~rough surface grain diameter of~~ surface roughness due to grains on an outer surface of said electrode is ~~formed so as to be~~ larger than a ~~rough surface grain diameter~~ surface roughness of an inner surface ~~thereof~~ of said electrode.

2. (Original) The semiconductor device according to claim 1, wherein a conductor film is formed along the inner surface of said electrode.

3. (Original) The semiconductor device according to claim 1, wherein the inner side of said cylindrical portion is buried with a conductive film.

4. (Currently Amended) A semiconductor device comprising:

an electrode formed of a cylindrical portion and a conductive film buried in [[the]] an inner side of said cylindrical portion, wherein a ~~rough surface grain diameter of~~ surface roughness due to gains on an outer surface of said ~~cylindrical~~

~~portion~~ electrode is ~~formed so as to be~~ larger than a ~~rough surface grain diameter of~~ surface roughness on an inner surface ~~thereof~~ of the electrode .

5. (Canceled)

6. (Canceled)

7. (Canceled)

8. (Canceled)

9. (Canceled)

10. (Canceled)

11. (New) A semiconductor device comprising:

an electrode formed of a flat plate portion at a bottom thereof and a cylindrical portion which extends up continuously from the flat plate portion and whose one side is open, wherein the surface area of an outer surface of said electrode is formed so as to be larger based on growth nuclei than the surface area of the reverse surface thereof.

12. (New) The semiconductor device according to claim 11, wherein a conductor film is formed along the inner surface of said electrode.

13. (New) The semiconductor device according to claim 11, wherein the inner side of said cylindrical portion is buried with a conductive film.

14. (New) A semiconductor device comprising:

an electrode formed of a cylindrical portion and a conductive film buried in an inner side of said cylindrical portion, wherein a surface area of an outer surface of said electrode is larger, based upon growth nuclei, than a surface area of a reverse surface thereof.